TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS V-H)

ТРСС8001-Н

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q_{SW} = 7.1 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS(ON)}$ = 7.6 m Ω (typ.) (V_{GS} = 4.5 V)

- High forward transfer admittance: |Y_{fs}| = 65 S (typ.)
- Low leakage current: I_{DSS} = 10 μ A (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_D = 1 mA)

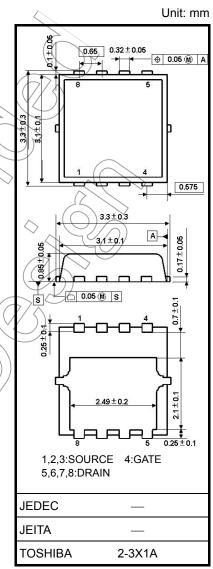
Absolute Maximum Ratings (Ta = 25°C)

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Characteristic		Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	30	N
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		VDGR	30	$\langle \langle v \rangle$
Gate-source voltage		VGSS	±20	X
Drain current	DC (Note 1)		22	Α
	Pulsed (Note 1)		66 <	
Drain power dissipation (Tc = 25°C)		PD	30	Ŵ
Drain power dissipation (t = 10 s) (Note 2a)		P P	1.9	w
Drain power dissipation (t = 10 s) (Note 2b)		PD <	0.7	W
Single-pulse avalanche energy (Note'3)		EAS	126	mJ
Avalanche current		I _{AR}	22	А
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	2.1	mJ
Channel temperature		Tch	150	°C
Storage temperature range		Tstg	–55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

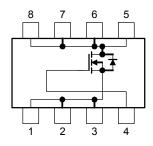
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

Circuit Configuration

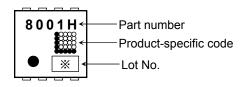


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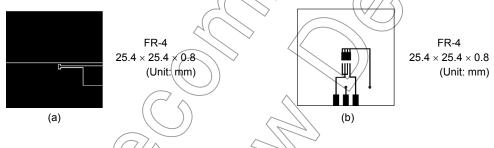
Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R _{th (ch-c)}	4.2	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	66	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	180	°C/W

Marking (Note 5)



- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: (a) Device mounted on a glass-epoxy board (a)



(b) Device mounted on a glass-epoxy board (b)

- Note 3: $V_{DD} = 24 \text{ V}, \text{ T}_{eh} = 25^{\circ}\text{C}$ (initial), $L = 200 \text{ }\mu\text{H}, \text{ R}_{G} = 25 \Omega, \text{ H}_{AR} = 22 \text{ A}$
- Note 4: Repetitive rating: pulse width limited by maximum channel temperature
- Note 5: * Weekly code: (Three digits)



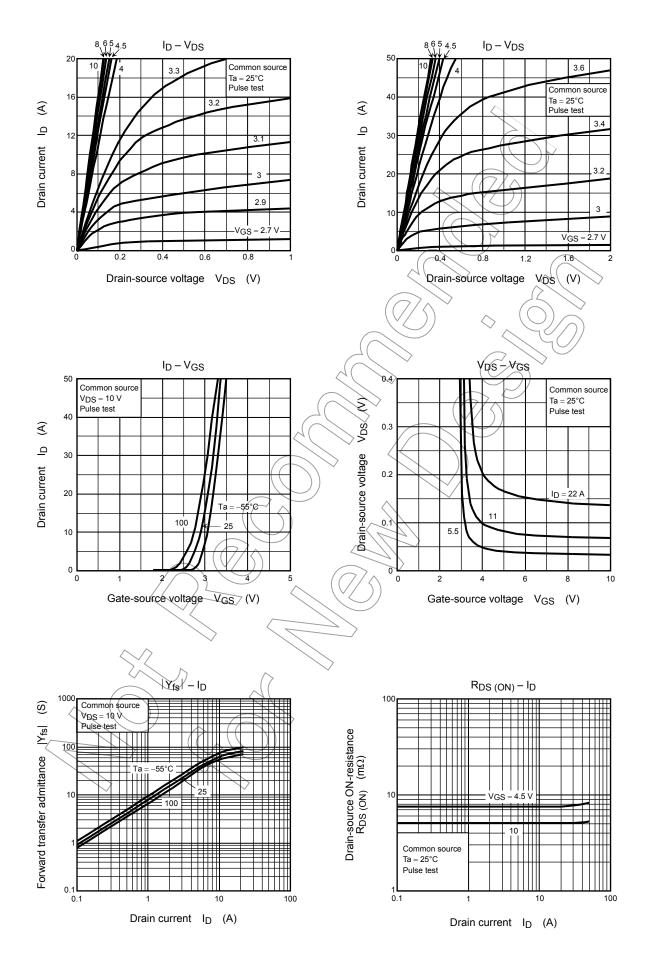
Electrical Characteristics (Ta = 25°C)

Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS}=\pm 20~V,~V_{DS}=0~V$	_	—	±100	nA
Drain cutoff curre	ent	I _{DSS}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_		10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—	_	v
		V (BR) DSX	$I_D = 10$ mA, $V_{GS} = -20$ V	15		_	v
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.5	-7(2.5	V
Drain-source ON-resistance		R _{DS (ON)}	$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$	\sim	7.6	10.6	mO
			$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	\mathcal{A}	5.5	8.3	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 11 A	33	65	_	S
Input capacitance		C _{iss}			1900	2500	
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	110	170	pF
Output capacitance		Coss			400	\searrow	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	-6	1.0) 1.5	Ω
Switching time	Rise time	tr		X	2.8) _	
	Turn-on time	t _{on}		$\langle \hat{\boldsymbol{\beta}} \rangle$	9.8	_	ne
	Fall time	t _f			5.9	_	ns
	Turn-off time	toff	Duty \leq 1%, t _w = 10 μ s	_	27	—	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 22 \text{ A}$		27		
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} \neq 22 \text{ A}$		14.3		
Gate-source char	rge 1	Qgs1		_	6.8		nC
Gate-drain ("Mille	er") charge	Qgd	$V_{DD} \approx 24 V, V_{GS} = 10 V, I_D = 22 A$	_	4.3		
Gate switch charg	ge (77	Q _{SW}		_	7.1	_	

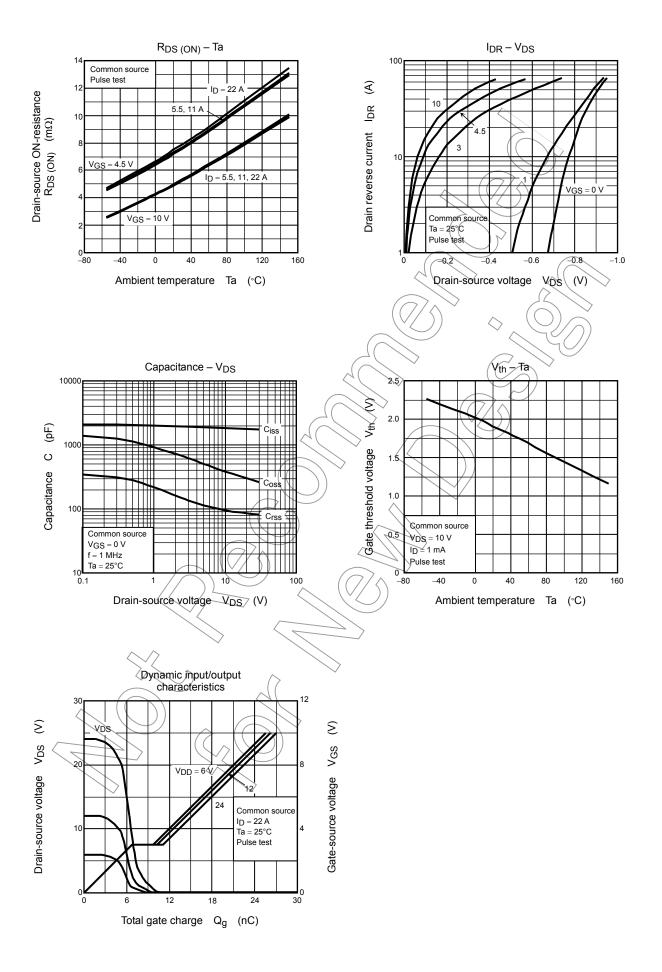
Source-Drain Ratings and Characteristics (Ta = 25° C)

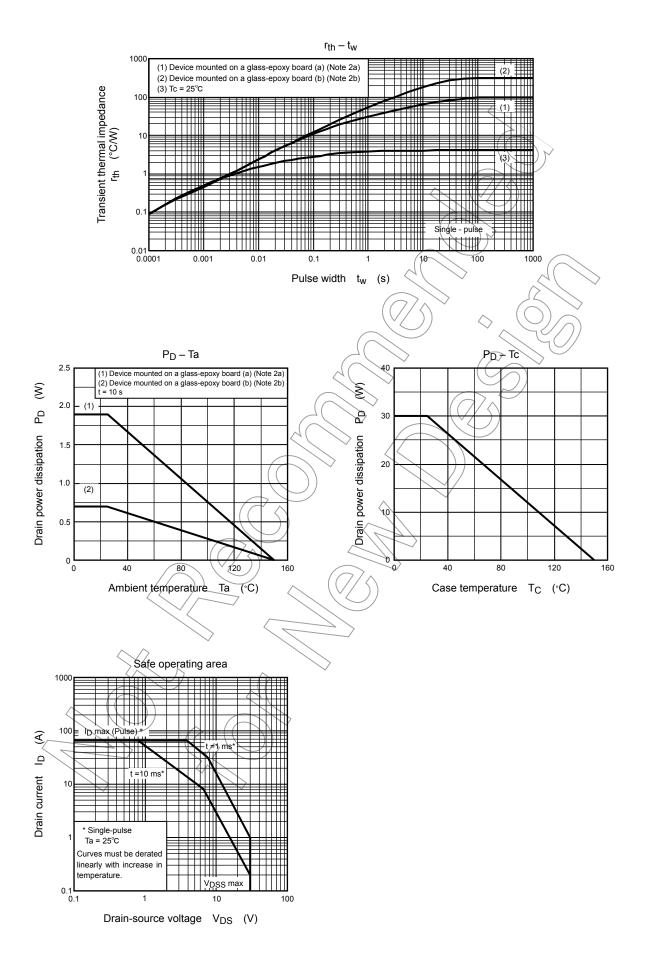
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I _{DRP}	> –	_	_	66	А
Forward voltage (diode)	VDSF	I _{DR} = 22 A, V _{GS} = 0 V			-1.2	V

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